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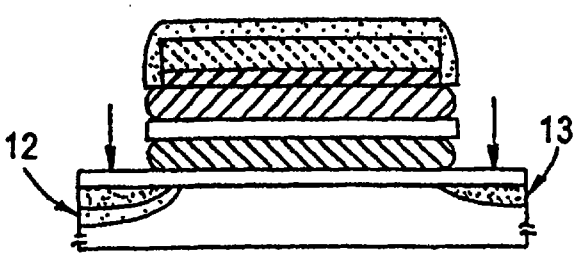
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(54) Title: ENCAPSULATED TUNGSTEN GATE MOS TRANSISTOR AND MEMORY CELL AND METHOD OF MAKING SAME

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(57) Abstract: A tungsten gate MOS transistor and a memory cell useful in flash EEPROM devices are fabricated by encapsulating the tungsten gate electrode contact of each of the MOS transistor and floating gate memory cell by silicon nitride capping and sidewall layers. The inventive methodology advantageously prevents deleterious oxidation during subsequent processing at high temperature and in an oxidizing ambient.